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Understanding <u>Embedded - FPGAs (Field Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	216
Number of Logic Elements/Cells	1728
Total RAM Bits	24576
Number of I/O	220
Number of Gates	119000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	484-BBGA
Supplier Device Package	484-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k30efi484-3

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Application	Resourc	es Used	Performance			Units
	LEs	EABs	-1 Speed Grade	-2 Speed Grade	-3 Speed Grade	
16-bit loadable counter	16	0	285	250	200	MHz
16-bit accumulator	16	0	285	250	200	MHz
16-to-1 multiplexer (1)	10	0	3.5	4.9	7.0	ns
16-bit multiplier with 3-stage pipeline (2)	592	0	156	131	93	MHz
256 × 16 RAM read cycle speed (2)	0	1	196	154	118	MHz
256 × 16 RAM write cycle	0	1	185	143	106	MHz

Notes:

- (1) This application uses combinatorial inputs and outputs.
- (2) This application uses registered inputs and outputs.

Table 6 shows FLEX 10KE performance for more complex designs. These designs are available as Altera MegaCore $^{\circ}$ functions.

Table 6. FLEX 10KE Performance for Complex Designs						
Application	LEs Used		Performance		Units	
		-1 Speed Grade	-2 Speed Grade	-3 Speed Grade		
8-bit, 16-tap parallel finite impulse response (FIR) filter	597	192	156	116	MSPS	
8-bit, 512-point fast Fourier	1,854	23.4	28.7	38.9	μ s (1)	
transform (FFT) function		113	92	68	MHz	
a16450 universal asynchronous receiver/transmitter (UART)	342	36	28	20.5	MHz	

Note:

(1) These values are for calculation time. Calculation time = number of clocks required / f_{max} . Number of clocks required = ceiling [log 2 (points)/2] × [points +14 + ceiling]

Figure 1 shows a block diagram of the FLEX 10KE architecture. Each group of LEs is combined into an LAB; groups of LABs are arranged into rows and columns. Each row also contains a single EAB. The LABs and EABs are interconnected by the FastTrack Interconnect routing structure. IOEs are located at the end of each row and column of the FastTrack Interconnect routing structure.

Embedded Array Block (EAB) I/O Element IOE IOE IOE IOE IOE IOE IOE IOE IOE (IOE) IOE Column Logic Array Interconnect EAB Logic Array Block (LAB) IOE Logic Element (LE) Row EAB Interconnect Local Interconnect Logic Array

Figure 1. FLEX 10KE Device Block Diagram

IOE

IOE

IOE

IOE

IOE

IOE

Embedded Array

FLEX 10KE devices provide six dedicated inputs that drive the flipflops' control inputs and ensure the efficient distribution of high-speed, low-skew (less than 1.5 ns) control signals. These signals use dedicated routing channels that provide shorter delays and lower skews than the FastTrack Interconnect routing structure. Four of the dedicated inputs drive four global signals. These four global signals can also be driven by internal logic, providing an ideal solution for a clock divider or an internally generated asynchronous clear signal that clears many registers in the device.

IOE

IOE

Embedded Array Block

The EAB is a flexible block of RAM, with registers on the input and output ports, that is used to implement common gate array megafunctions. Because it is large and flexible, the EAB is suitable for functions such as multipliers, vector scalars, and error correction circuits. These functions can be combined in applications such as digital filters and microcontrollers.

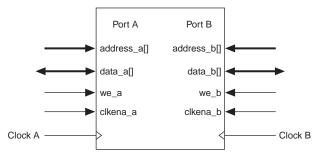
Logic functions are implemented by programming the EAB with a read-only pattern during configuration, thereby creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement any function with 8 inputs and 16 outputs. Parameterized functions such as LPM functions can take advantage of the EAB automatically.

The FLEX 10KE EAB provides advantages over FPGAs, which implement on-board RAM as arrays of small, distributed RAM blocks. These small FPGA RAM blocks must be connected together to make RAM blocks of manageable size. The RAM blocks are connected together using multiplexers implemented with more logic blocks. These extra multiplexers cause extra delay, which slows down the RAM block. FPGA RAM blocks are also prone to routing problems because small blocks of RAM must be connected together to make larger blocks. In contrast, EABs can be used to implement large, dedicated blocks of RAM that eliminate these timing and routing concerns.

The FLEX 10KE enhanced EAB adds dual-port capability to the existing EAB structure. The dual-port structure is ideal for FIFO buffers with one or two clocks. The FLEX 10KE EAB can also support up to 16-bit-wide RAM blocks and is backward-compatible with any design containing FLEX 10K EABs. The FLEX 10KE EAB can act in dual-port or single-port mode. When in dual-port mode, separate clocks may be used for EAB read and write sections, which allows the EAB to be written and read at different rates. It also has separate synchronous clock enable signals for the EAB read and write sections, which allow independent control of these sections.

The EAB can also use Altera megafunctions to implement dual-port RAM applications where both ports can read or write, as shown in Figure 3.

Figure 3. FLEX 10KE EAB in Dual-Port RAM Mode



The FLEX 10KE EAB can be used in a single-port mode, which is useful for backward-compatibility with FLEX 10K designs (see Figure 4).

The programmable flipflop in the LE can be configured for D, T, JK, or SR operation. The clock, clear, and preset control signals on the flipflop can be driven by global signals, general-purpose I/O pins, or any internal logic. For combinatorial functions, the flipflop is bypassed and the output of the LUT drives the output of the LE.

The LE has two outputs that drive the interconnect: one drives the local interconnect and the other drives either the row or column FastTrack Interconnect routing structure. The two outputs can be controlled independently. For example, the LUT can drive one output while the register drives the other output. This feature, called register packing, can improve LE utilization because the register and the LUT can be used for unrelated functions.

The FLEX 10KE architecture provides two types of dedicated high-speed data paths that connect adjacent LEs without using local interconnect paths: carry chains and cascade chains. The carry chain supports high-speed counters and adders and the cascade chain implements wide-input functions with minimum delay. Carry and cascade chains connect all LEs in a LAB as well as all LABs in the same row. Intensive use of carry and cascade chains can reduce routing flexibility. Therefore, the use of these chains should be limited to speed-critical portions of a design.

Carry Chain

The carry chain provides a very fast (as low as 0.2 ns) carry-forward function between LEs. The carry-in signal from a lower-order bit drives forward into the higher-order bit via the carry chain, and feeds into both the LUT and the next portion of the carry chain. This feature allows the FLEX 10KE architecture to implement high-speed counters, adders, and comparators of arbitrary width efficiently. Carry chain logic can be created automatically by the Altera Compiler during design processing, or manually by the designer during design entry. Parameterized functions such as LPM and DesignWare functions automatically take advantage of carry chains.

Carry chains longer than eight LEs are automatically implemented by linking LABs together. For enhanced fitting, a long carry chain skips alternate LABs in a row. A carry chain longer than one LAB skips either from even-numbered LAB to even-numbered LAB, or from odd-numbered LAB to odd-numbered LAB. For example, the last LE of the first LAB in a row carries to the first LE of the third LAB in the row. The carry chain does not cross the EAB at the middle of the row. For instance, in the EPF10K50E device, the carry chain stops at the eighteenth LAB and a new one begins at the nineteenth LAB.

Cascade Chain

With the cascade chain, the FLEX 10KE architecture can implement functions that have a very wide fan-in. Adjacent LUTs can be used to compute portions of the function in parallel; the cascade chain serially connects the intermediate values. The cascade chain can use a logical AND or logical OR (via De Morgan's inversion) to connect the outputs of adjacent LEs. An a delay as low as 0.6 ns per LE, each additional LE provides four more inputs to the effective width of a function. Cascade chain logic can be created automatically by the Altera Compiler during design processing, or manually by the designer during design entry.

Cascade chains longer than eight bits are implemented automatically by linking several LABs together. For easier routing, a long cascade chain skips every other LAB in a row. A cascade chain longer than one LAB skips either from even-numbered LAB to even-numbered LAB, or from odd-numbered LAB to odd-numbered LAB (e.g., the last LE of the first LAB in a row cascades to the first LE of the third LAB). The cascade chain does not cross the center of the row (e.g., in the EPF10K50E device, the cascade chain stops at the eighteenth LAB and a new one begins at the nineteenth LAB). This break is due to the EAB's placement in the middle of the row.

Figure 10 shows how the cascade function can connect adjacent LEs to form functions with a wide fan-in. These examples show functions of 4n variables implemented with n LEs. The LE delay is 0.9 ns; the cascade chain delay is 0.6 ns. With the cascade chain, 2.7 ns are needed to decode a 16-bit address.

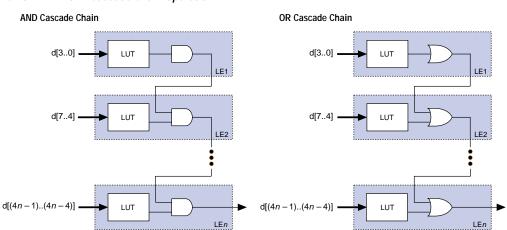
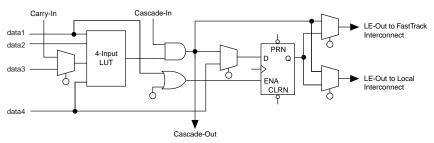


Figure 10. FLEX 10KE Cascade Chain Operation

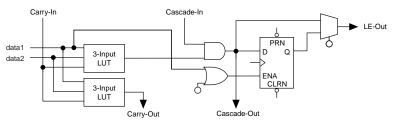
Figure 11 shows the LE operating modes.

Figure 11. FLEX 10KE LE Operating Modes

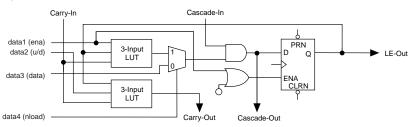
Normal Mode



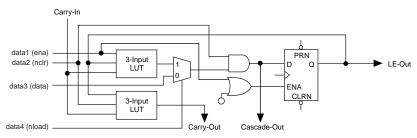
Arithmetic Mode



Up/Down Counter Mode



Clearable Counter Mode



For improved routing, the row interconnect consists of a combination of full-length and half-length channels. The full-length channels connect to all LABs in a row; the half-length channels connect to the LABs in half of the row. The EAB can be driven by the half-length channels in the left half of the row and by the full-length channels. The EAB drives out to the full-length channels. In addition to providing a predictable, row-wide interconnect, this architecture provides increased routing resources. Two neighboring LABs can be connected using a half-row channel, thereby saving the other half of the channel for the other half of the row.

Table 7 summarizes the FastTrack Interconnect routing structure resources available in each FLEX 10KE device.

Table 7. FLEX 1	Table 7. FLEX 10KE FastTrack Interconnect Resources							
Device	Rows	Channels per Row	Columns	Channels per Column				
EPF10K30E	6	216	36	24				
EPF10K50E EPF10K50S	10	216	36	24				
EPF10K100E	12	312	52	24				
EPF10K130E	16	312	52	32				
EPF10K200E EPF10K200S	24	312	52	48				

In addition to general-purpose I/O pins, FLEX 10KE devices have six dedicated input pins that provide low-skew signal distribution across the device. These six inputs can be used for global clock, clear, preset, and peripheral output enable and clock enable control signals. These signals are available as control signals for all LABs and IOEs in the device. The dedicated inputs can also be used as general-purpose data inputs because they can feed the local interconnect of each LAB in the device.

Figure 14 shows the interconnection of adjacent LABs and EABs, with row, column, and local interconnects, as well as the associated cascade and carry chains. Each LAB is labeled according to its location: a letter represents the row and a number represents the column. For example, LAB B3 is in row B, column 3.

When dedicated inputs drive non-inverted and inverted peripheral clears, clock enables, and output enables, two signals on the peripheral control bus will be used.

Tables 8 and 9 list the sources for each peripheral control signal, and show how the output enable, clock enable, clock, and clear signals share 12 peripheral control signals. The tables also show the rows that can drive global signals.

Peripheral Control Signal	EPF10K30E	EPF10K50E EPF10K50S
OE0	Row A	Row A
OE1	Row B	Row B
OE2	Row C	Row D
OE3	Row D	Row F
OE4	Row E	Row H
OE5	Row F	Row J
CLKENA0/CLK0/GLOBAL0	Row A	Row A
CLKENA1/OE6/GLOBAL1	Row B	Row C
CLKENA2/CLR0	Row C	Row E
CLKENA3/OE7/GLOBAL2	Row D	Row G
CLKENA4/CLR1	Row E	Row I
CLKENA5/CLK1/GLOBAL3	Row F	Row J

The VCCINT pins must always be connected to a 2.5-V power supply. With a 2.5-V $V_{\rm CCINT}$ level, input voltages are compatible with 2.5-V, 3.3-V, and 5.0-V inputs. The VCCIO pins can be connected to either a 2.5-V or 3.3-V power supply, depending on the output requirements. When the VCCIO pins are connected to a 2.5-V power supply, the output levels are compatible with 2.5-V systems. When the VCCIO pins are connected to a 3.3-V power supply, the output high is at 3.3 V and is therefore compatible with 3.3-V or 5.0-V systems. Devices operating with $V_{\rm CCIO}$ levels higher than 3.0 V achieve a faster timing delay of t_{OD2} instead of t_{OD1} .

Table 14 summarizes FLEX 10KE MultiVolt I/O support.

Table 14. FLEX 10KE MultiVolt I/O Support							
V _{CCIO} (V) Input Signal (V) Output Signal (V)							
	2.5	3.3	5.0	2.5	3.3	5.0	
2.5	✓	√ (1)	√ (1)	✓			
3.3	✓	✓	√ (1)	√ (2)	✓	✓	

Notes:

- (1) The PCI clamping diode must be disabled to drive an input with voltages higher than $V_{\rm CCIO}$.
- (2) When $V_{\rm CCIO}$ = 3.3 V, a FLEX 10KE device can drive a 2.5-V device that has 3.3-V tolerant inputs.

Open-drain output pins on FLEX 10KE devices (with a pull-up resistor to the 5.0-V supply) can drive 5.0-V CMOS input pins that require a $V_{\rm IH}$ of 3.5 V. When the open-drain pin is active, it will drive low. When the pin is inactive, the trace will be pulled up to 5.0 V by the resistor. The open-drain pin will only drive low or tri-state; it will never drive high. The rise time is dependent on the value of the pull-up resistor and load impedance. The $I_{\rm OL}$ current specification should be considered when selecting a pull-up resistor.

Power Sequencing & Hot-Socketing

Because FLEX 10KE devices can be used in a mixed-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. The $V_{\rm CCIO}$ and $V_{\rm CCINT}$ power planes can be powered in any order.

Signals can be driven into FLEX 10KE devices before and during power up without damaging the device. Additionally, FLEX 10KE devices do not drive out during power up. Once operating conditions are reached, FLEX 10KE devices operate as specified by the user.

to Be Driven

Figure 20. FLEX 10KE JTAG Waveforms TMS TDI t_{JPSU} TCK t_{JPZX} t _{JPXZ} $\mathbf{t}_{\mathsf{JPCO}}$ TDO t_{JSH} t_{JSSU} Signal to Be Captured t_{JSCO}t_{JSZX} t_{JSXZ} Signal

Figure 20 shows the timing requirements for the JTAG signals.

Table 18 shows the timing parameters and values for FLEX 10KE devices.

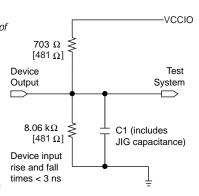
Table 1	8. FLEX 10KE JTAG Timing Parameters & Values			
Symbol	Parameter	Min	Max	Unit
t _{JCP}	TCK clock period	100		ns
t _{JCH}	TCK clock high time	50		ns
t _{JCL}	TCK clock low time	50		ns
t _{JPSU}	JTAG port setup time	20		ns
t _{JPH}	JTAG port hold time	45		ns
t _{JPCO}	JTAG port clock to output		25	ns
t _{JPZX}	JTAG port high impedance to valid output		25	ns
t _{JPXZ}	JTAG port valid output to high impedance		25	ns
t _{JSSU}	Capture register setup time	20		ns
t _{JSH}	Capture register hold time	45		ns
t _{JSCO}	Update register clock to output		35	ns
t _{JSZX}	Update register high impedance to valid output		35	ns
t _{JSXZ}	Update register valid output to high impedance		35	ns

Generic Testing

Each FLEX 10KE device is functionally tested. Complete testing of each configurable static random access memory (SRAM) bit and all logic functionality ensures 100% yield. AC test measurements for FLEX 10KE devices are made under conditions equivalent to those shown in Figure 21. Multiple test patterns can be used to configure devices during all stages of the production flow.

Figure 21. FLEX 10KE AC Test Conditions

Power supply transients can affect AC measurements. Simultaneous transitions of multiple outputs should be avoided for accurate measurement. Threshold tests must not be performed under AC conditions. Large-amplitude, fast-groundcurrent transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result. Numbers in brackets are for 2.5-V devices or outputs. Numbers without brackets are for 3.3-V. devices or outputs.



Operating Conditions

Tables 19 through 23 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 2.5-V FLEX 10KE devices.

Table 19	9. FLEX 10KE 2.5-V Device A	Absolute Maximum Ratings Note (1)			
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CCINT}	Supply voltage	With respect to ground (2)	-0.5	3.6	V
V _{CCIO}			-0.5	4.6	V
VI	DC input voltage		-2.0	5.75	V
I _{OUT}	DC output current, per pin		-25	25	mA
T _{STG}	Storage temperature	No bias	-65	150	° C
T _{AMB}	Ambient temperature	Under bias	-65	135	°C
TJ	Junction temperature	PQFP, TQFP, BGA, and FineLine BGA		135	°C
		packages, under bias		450	
		Ceramic PGA packages, under bias		150	° C

Figure 25. FLEX 10KE Device LE Timing Model

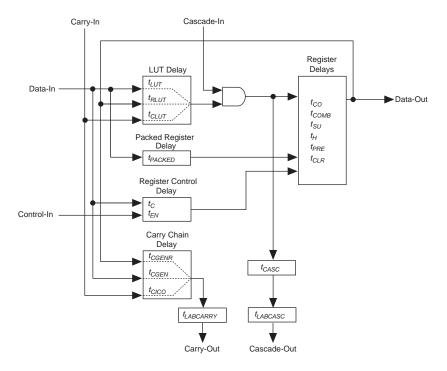


Table 24. LE	Timing Microparameters (Part 2 of 2) Note (1)	
Symbol	Parameter	Condition
t _{CLR}	LE register clear delay	
t _{CH}	Minimum clock high time from clock pin	
t_{CL}	Minimum clock low time from clock pin	

Table 25. 10	E Timing Microparameters Note (1)	
Symbol	Parameter	Conditions
t_{IOD}	IOE data delay	
t _{IOC}	IOE register control signal delay	
t _{IOCO}	IOE register clock-to-output delay	
t _{IOCOMB}	IOE combinatorial delay	
t _{IOSU}	IOE register setup time for data and enable signals before clock; IOE register recovery time after asynchronous clear	
t _{IOH}	IOE register hold time for data and enable signals after clock	
t _{IOCLR}	IOE register clear time	
t _{OD1}	Output buffer and pad delay, slow slew rate = off, V _{CCIO} = 3.3 V	C1 = 35 pF (2)
t_{OD2}	Output buffer and pad delay, slow slew rate = off, V _{CCIO} = 2.5 V	C1 = 35 pF (3)
t _{OD3}	Output buffer and pad delay, slow slew rate = on	C1 = 35 pF (4)
t_{XZ}	IOE output buffer disable delay	
t _{ZX1}	IOE output buffer enable delay, slow slew rate = off, V _{CCIO} = 3.3 V	C1 = 35 pF (2)
t_{ZX2}	IOE output buffer enable delay, slow slew rate = off, V _{CCIO} = 2.5 V	C1 = 35 pF (3)
t _{ZX3}	IOE output buffer enable delay, slow slew rate = on	C1 = 35 pF (4)
t _{INREG}	IOE input pad and buffer to IOE register delay	
t _{IOFD}	IOE register feedback delay	
t _{INCOMB}	IOE input pad and buffer to FastTrack Interconnect delay	

Table 27. EAB	B Timing Macroparameters Note (1), (6)					
Symbol	Parameter	Conditions				
t _{EABAA}	EAB address access delay					
t _{EABRCCOMB}	EAB asynchronous read cycle time					
t _{EABRCREG}	EAB synchronous read cycle time					
t_{EABWP}	EAB write pulse width					
$t_{EABWCCOMB}$	EAB asynchronous write cycle time					
t _{EABWCREG}	EAB synchronous write cycle time					
t _{EABDD}	EAB data-in to data-out valid delay					
t _{EABDATA} CO	EAB clock-to-output delay when using output registers					
t _{EABDATASU}	EAB data/address setup time before clock when using input register					
t _{EABDATAH}	EAB data/address hold time after clock when using input register					
t _{EABWESU}	EAB WE setup time before clock when using input register					
t _{EABWEH}	EAB WE hold time after clock when using input register					
t _{EABWDSU}	EAB data setup time before falling edge of write pulse when not using input registers					
t _{EABWDH}	EAB data hold time after falling edge of write pulse when not using input registers					
t _{EABWASU}	EAB address setup time before rising edge of write pulse when not using input registers					
t _{EABWAH}	EAB address hold time after falling edge of write pulse when not using input registers					
t _{EABWO}	EAB write enable to data output valid delay					

Symbol	-1 Spee	-1 Speed Grade		-2 Speed Grade		ed Grade	Unit
	Min	Max	Min	Max	Min	Max	
t _{EABDATA1}		1.7		2.0		2.3	ns
t _{EABDATA1}		0.6		0.7		0.8	ns
t _{EABWE1}		1.1		1.3		1.4	ns
t _{EABWE2}		0.4		0.4		0.5	ns
t _{EABRE1}		0.8		0.9		1.0	ns
t _{EABRE2}		0.4		0.4		0.5	ns
t _{EABCLK}		0.0		0.0		0.0	ns
t _{EABCO}		0.3		0.3		0.4	ns
t _{EABBYPASS}		0.5		0.6		0.7	ns
t _{EABSU}	0.9		1.0		1.2		ns
t _{EABH}	0.4		0.4		0.5		ns
t _{EABCLR}	0.3		0.3		0.3		ns
t_{AA}		3.2		3.8		4.4	ns
t_{WP}	2.5		2.9		3.3		ns
t_{RP}	0.9		1.1		1.2		ns
t _{WDSU}	0.9		1.0		1.1		ns
t _{WDH}	0.1		0.1		0.1		ns
t _{WASU}	1.7		2.0		2.3		ns
t _{WAH}	1.8		2.1		2.4		ns
t _{RASU}	3.1		3.7		4.2		ns
t _{RAH}	0.2		0.2		0.2		ns
t _{WO}		2.5		2.9		3.3	ns
t _{DD}		2.5		2.9		3.3	ns
t _{EABOUT}		0.5		0.6		0.7	ns
t _{EABCH}	1.5		2.0		2.3		ns
t _{EABCL}	2.5		2.9		3.3		ns

Table 38. EPF10K	50E Device	LE Timing M	licroparame	ters (Part 2	of 2) No	te (1)	
Symbol	-1 Spee	d Grade	-2 Speed Grade -3 Speed Grade		Unit		
	Min	Max	Min	Max	Min	Max	
t_H	0.9		1.0		1.4		ns
t _{PRE}		0.5		0.6		0.8	ns
t _{CLR}		0.5		0.6		0.8	ns
t _{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns

Table 39. EPF10K50E Device IOE Timing Microparameters Note (1)								
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit	
	Min	Max	Min	Max	Min	Max		
t_{IOD}		2.2		2.4		3.3	ns	
t _{IOC}		0.3		0.3		0.5	ns	
t_{IOCO}		1.0		1.0		1.4	ns	
t _{IOCOMB}		0.0		0.0		0.2	ns	
t _{IOSU}	1.0		1.2		1.7		ns	
t _{IOH}	0.3		0.3		0.5		ns	
t _{IOCLR}		0.9		1.0		1.4	ns	
t _{OD1}		0.8		0.9		1.2	ns	
t _{OD2}		0.3		0.4		0.7	ns	
t _{OD3}		3.0		3.5		3.5	ns	
t_{XZ}		1.4		1.7		2.3	ns	
t_{ZX1}		1.4		1.7		2.3	ns	
t _{ZX2}		0.9		1.2		1.8	ns	
t _{ZX3}		3.6		4.3		4.6	ns	
t _{INREG}		4.9		5.8		7.8	ns	
t _{IOFD}		2.8		3.3		4.5	ns	
t _{INCOMB}		2.8		3.3		4.5	ns	

Table 56. EPF10K130E Device Interconnect Timing Microparameters Note (1)								
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit	
	Min	Max	Min	Max	Min	Max		
t _{DIN2IOE}		2.8		3.5		4.4	ns	
t _{DIN2LE}		0.7		1.2		1.6	ns	
t _{DIN2DATA}		1.6		1.9		2.2	ns	
t _{DCLK2IOE}		1.6		2.1		2.7	ns	
t _{DCLK2LE}		0.7		1.2		1.6	ns	
t _{SAMELAB}		0.1		0.2		0.2	ns	
t _{SAMEROW}		1.9		3.4		5.1	ns	
t _{SAME} COLUMN		0.9		2.6		4.4	ns	
t _{DIFFROW}		2.8		6.0		9.5	ns	
t _{TWOROWS}		4.7		9.4		14.6	ns	
t _{LEPERIPH}		3.1		4.7		6.9	ns	
t _{LABCARRY}		0.6		0.8		1.0	ns	
t _{LABCASC}		0.9		1.2		1.6	ns	

Table 57. EPF10K130E External Timing ParametersNotes (1), (2)								
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit	
	Min	Max	Min	Max	Min	Max		
t _{DRR}		9.0		12.0		16.0	ns	
t _{INSU} (3)	1.9		2.1		3.0		ns	
t _{INH} (3)	0.0		0.0		0.0		ns	
t _{outco} (3)	2.0	5.0	2.0	7.0	2.0	9.2	ns	
t _{INSU} (4)	0.9		1.1		-		ns	
t _{INH} (4)	0.0		0.0		-		ns	
t _{OUTCO} (4)	0.5	4.0	0.5	6.0	-	-	ns	
t _{PCISU}	3.0		6.2		-		ns	
t _{PCIH}	0.0		0.0		-		ns	
t _{PCICO}	2.0	6.0	2.0	6.9	_	_	ns	

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{INSUBIDIR} (3)	2.2		2.4		3.2		ns
t _{INHBIDIR} (3)	0.0		0.0		0.0		ns
t _{INSUBIDIR} (4)	2.8		3.0		-		ns
t _{INHBIDIR} (4)	0.0		0.0		-		ns
t _{OUTCOBIDIR} (3)	2.0	5.0	2.0	7.0	2.0	9.2	ns
t _{XZBIDIR} (3)		5.6		8.1		10.8	ns
t _{ZXBIDIR} (3)		5.6		8.1		10.8	ns
toutcobidir (4)	0.5	4.0	0.5	6.0	-	_	ns
t _{XZBIDIR} (4)		4.6		7.1		-	ns
t _{ZXBIDIR} (4)		4.6		7.1		-	ns

Notes to tables:

- (1) All timing parameters are described in Tables 24 through 30 in this data sheet.
- (2) These parameters are specified by characterization.
- (3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
- (4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Tables 59 through 65 show EPF10K200E device internal and external timing parameters.

Symbol	-1 Spee	-1 Speed Grade		-2 Speed Grade		ed Grade	Unit
	Min	Max	Min	Max	Min	Max	
t _{LUT}		0.7		0.8		1.2	ns
t _{CLUT}		0.4		0.5		0.6	ns
t _{RLUT}		0.6		0.7		0.9	ns
t _{PACKED}		0.3		0.5		0.7	ns
t_{EN}		0.4		0.5		0.6	ns
t _{CICO}		0.2		0.2		0.3	ns
t _{CGEN}		0.4		0.4		0.6	ns
t _{CGENR}		0.2		0.2		0.3	ns
t _{CASC}		0.7		0.8		1.2	ns
t_{C}		0.5		0.6		0.8	ns
t_{CO}		0.5		0.6		0.8	ns
t _{СОМВ}		0.4		0.6		0.8	ns
t_{SU}	0.4		0.6		0.7		ns

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{DRR}		8.0		9.5		12.5	ns
t _{INSU} (2)	2.4		2.9		3.9		ns
t _{INH} (2)	0.0		0.0		0.0		ns
t _{оитсо} (2)	2.0	4.3	2.0	5.2	2.0	7.3	ns
t _{INSU} (3)	2.4		2.9				ns
t _{INH} (3)	0.0		0.0				ns
t _{оитсо} (3)	0.5	3.3	0.5	4.1			ns
t _{PCISU}	2.4		2.9		_		ns
t _{PCIH}	0.0		0.0		_		ns
t _{PCICO}	2.0	6.0	2.0	7.7	_	-	ns

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{INSUBIDIR} (2)	2.7		3.2		4.3		ns
t _{INHBIDIR} (2)	0.0		0.0		0.0		ns
t _{INHBIDIR} (3)	0.0		0.0		-		ns
t _{INSUBIDIR} (3)	3.7		4.2		-		ns
toutcobidir (2)	2.0	4.5	2.0	5.2	2.0	7.3	ns
t _{XZBIDIR} (2)		6.8		7.8		10.1	ns
t _{ZXBIDIR} (2)		6.8		7.8		10.1	ns
toutcobidir (3)	0.5	3.5	0.5	4.2	-	-	
xzbidir (3)		6.8		8.4		-	ns
t _{ZXBIDIR} (3)		6.8		8.4		_	ns

Notes to tables:

- All timing parameters are described in Tables 24 through 30. This parameter is measured without use of the ClockLock or ClockBoost circuits.
- This parameter is measured with use of the ClockLock or ClockBoost circuits (3)